

NXH010P90MNF1

SiC Module, 2-PACK Half Bridge Topology, 900 V, 10 mohm
SiC M2 MOSFET

The NXH010P90MNF1 is a SiC MOSFET module containing a 10 mohm 900V SiC MOSFET half bridge and an NTC thermistor in an F1 module.

- Recommended gate voltage 15V - 18V
 - Low thermal resistance
 - Options for TIM or no TIM
- Improved RDS(ON) at higher voltage
 - Improved efficiency or higher power density
 - Flexible solution for high reliability thermal interface
- AC-DC Conversion
 - DC-AC Conversion
 - DC-DC Conversion
- Electric Vehicle Charger
 - Energy Storage System
 - Solar Inverter 3-phase
 - Uninterruptible Power Supply

	Pricing (\$/Unit)	Compliance	Status	Configuration	V _{BR} Max (V)	R _{DS(on)} Typ (mΩ)	Application	Package Type
NXH010P90MNF1PG	103.1308	Pb H	NEW	2-PACK	900	10	EV Charging, Energy Infrastructure	PIM18 33.8x42.5 (PRESS FIT)
NXH010P90MNF1PTG	103.1308	Pb H	NEW	2-PACK	900	10	EV Charging, Energy Infrastructure	PIM18 33.8x42.5 (PRESS FIT)